

# 产品规格书

# SPECIFICATIONS FOR PRODUCT

产品类型 TYPE : SMD3225

产品规格 SPEC : 12MHz/3225/12PF/10PPM

产品型号 P/N : CJ13-120001210B20

日期 DATE : 2021/05/06

| 核准及签名                |                  |                   | 番り、フ    |
|----------------------|------------------|-------------------|---------|
| R&D APPR. SIGNATURED |                  |                   | DEPT.   |
| 拟制                   | 审核               | 批准                | 频率器件事业部 |
| ISSUE                | CHECK            | APPROVAL          |         |
| Ivan 2021/05/06      | Abbey 2021/05/06 | Ken<br>2021/05/06 |         |

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### JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD

# SMCE3225 4 pads Crystal Resonator

## CJ13-120001210B20

### 1. Scope:

1.1 This specification applies to the RoHS/SONY compliance quartz crystal unit with a frequency of 12MHz which will be used in crystal oscillator applications.

#### 2. Construction:

2.1 Type of Quartz Resonator: SMCE3225 4pads

#### 3. Electrical Characteristics

3.1 Nominal Frequency(f): 12.000MHz

3.2 Load Capacitance(C<sub>L</sub>): 12pF

3.3 Frequency Tolerance(△f/f): ±10ppm

3.4 Frequency Temperature Stability: ±20ppm

3.5 Resonance Resistance(ohm): 80ohms Max

3.6 Osc mode: Fundamental mode

3.7 Shunt Capacitance( $C_0$ ): <2pF

3.8 Drive Level( $D_L$ ): <100 $\mu$ W

3.9 Operating Temperature Range( $T_{OPR}$ ): -40 to + 85

3.10 Storage Temperature Range( $T_{STG}$ ): -55 to + 125°C

3.11 Insulation Resistance(IR): >500 M ohms

3.12 Aging( $\triangle f_A$ ): ±3ppm per Year

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# 4. Reliability Specifications

This is the quality control and quality assurance and reliability tests performance data for the RoHS/

SONYcompliance 12MHz SMCE3225 4pads crystal resonators

related to the specification and approval sheet provided by JSCJ.

Standard test condition (TEMP.: 20±5°C. Relative humidity: 65±20%)

For any discrepancy in GO/NG, test will be done at TEMP.25±2°C, R.H. 65±5%.

| NO.  | PROCESS   | SPECIFICATION   | TEST METHOD  |
|------|---|---|--|
| 4.1  | Temperature Cycle (GB/T 2423.22-2002, Method Nb)                    | Frequency change after test ≤±<br>5ppm.Resonance resistance<br>change after test ≤10ohms.                         | taken after DUT being left at room temperature for 24±2 hours.   |
| 4.2  | Low Temperature Storage<br>(GB/T 2423.1-2001, Method<br>Aa)         | Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.                               | Spending 72 hrs at -55°C±3°C constant temperature. Measurement taken after DUT being left at room temperature for 24±2 hours.  |
| 4.3  | High Temperature Storage<br>(GB/T 2423.2-2001, Method<br>Ba)        | Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.                               | Spending 72 hrs at 125°C±3°C constant temperature. Measurement taken after DUT being left at room temperature for 24±2 hours.  |
| 4.4  | Humidity (GB/T 2423.3-<br>2006, Method Cab)                         | Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.                               | Spending 96 hrs at 40 °C $\pm$ 3 °C, with 93 %R.H, Then keep the DUT in dry oven at 40 $\pm$ 5 °C for 24 hour. Measurement taken after DUT being left at room temperature for 1 to 2 hours.  |
| 4.5  | Vibration (GB/T 2423.10-<br>1995, Method Fc)                        | Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.                               | Apply 0.75mm vibration at sweep frequency $10^{\sim}$ 500 Hz, 10 cycles in each direction of 3 axis. Measurement taken after 1 hour.   |
| 4.6  | Shock (GB/T 2423.5-1995,<br>Method Ea)                              | Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.and exhibit no visible damage. | Peak 1000m/s2, normal width 6ms half sine wave form, 3.7m/s, 3 perpendicular axis of samples, 3 cycles / direction, total 18 cycles. Measurement taken after 1 hour.   |
| 4.7  | Drop (GB/T 2423.8-1995,<br>Method Ed)                               | Frequency change after test ≤± 5ppm.Resonance resistance change after test ≤10ohms.and exhibit no visible damage. | Free drop to the steel plate with thickness of 3 mm from 1.00 m heights for 3 times.   |
| 4.8  | Solderability (IEC60068-2-58,Test Td:)                              | Terminals shall be covered more then 95% with solder.   | Passed through the re-flow oven under the following condition. Preheat 150 to 180°C for 60 to 120sec, and soldering time for 20s ± 5s at 235°C, peak soldering time for 10s ± 1s betweein 240 and 250°C. There is no need to do functional test. 8-12X magnifier.            |
| 4.9  | Terminal Strength (JIS-C-<br>6429 Method 1 & 2 )                    | No visible damage   | Mount on a glass-epoxy board (100x50x1.6mm), then bend to 2mm displacement (velocity 1mm/sec) and keep for 5 seconds. or pulling force 1.8kg for at least 60 seconds.  |
|      |   |   |  |
| 4.10 | Resistance to Soldering<br>Heat (IEC60068-2-58,Test<br>Td: Table 4) | Frequency change after test ≤±<br>5ppm.Resonance resistance<br>change after test ≤10ohms.                         | Passed through the re-flow oven under the following condition. Preheat 150 to 180°C for 60 to 120sec, and sodering time for 60s max at 235°C, peak soldering time for 20s max at 265°C max. Measurement taken after DUT being left at room temperature for at least 2 hours. |
|      |   |   |  |
| 4.11 | OTHERS  |   |  |

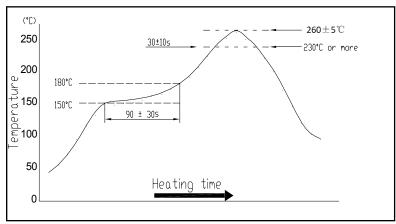
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#### **Recommended Reflow soldering condition**

## 5. Recommended Reflow soldering condition (SMD)

Solder profile

Peak: 260±5°C Soldering zone: 230°C or more, 30±10s. Pre-heating zone 1: 150 $\sim$  180°C, 90±30s



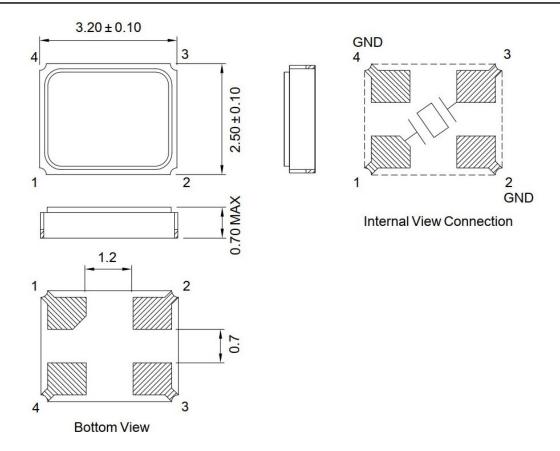
Temperature profile for reflow soldering

## 6. Soldering iron method

Bit temperature: 350±10°C Application time of soldering iron:3+1 s. For other procedures, refer to IEC 60068-2-20.

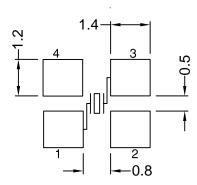
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## **Package Outline Dimensions**

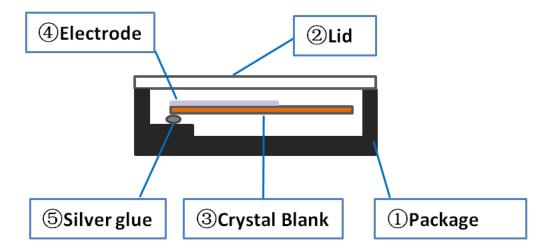


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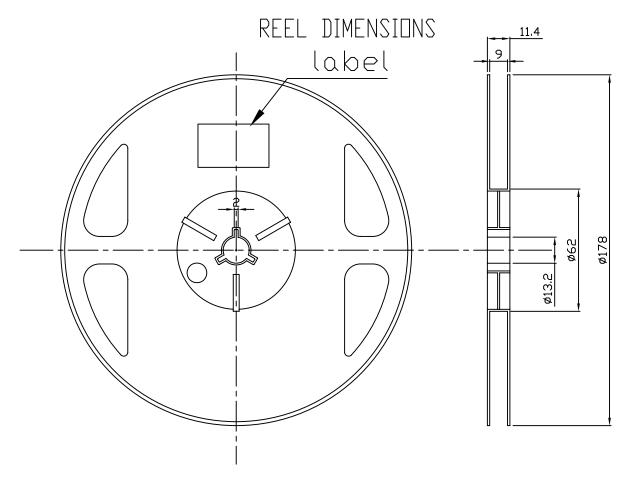
# Suggested Pad Layout



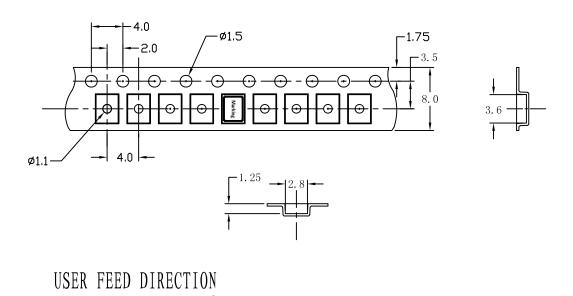
# **Inside Structure**



| No. | Components    | Materials                                |
|-----|---------------|--|
| 1   | Package       | Ceramic(Al <sub>2</sub> O <sub>3</sub> ) |
| 2   | Lid           | KV(Fe/Ni/Co)                             |
| 3   | Crystal blank | SiO <sub>2</sub>                         |
| 4   | Electrode     | Ag、Cr                                    |
| 5   | Silver glue   | Ag、CH <sub>3</sub> OH、SiO <sub>2</sub>   |

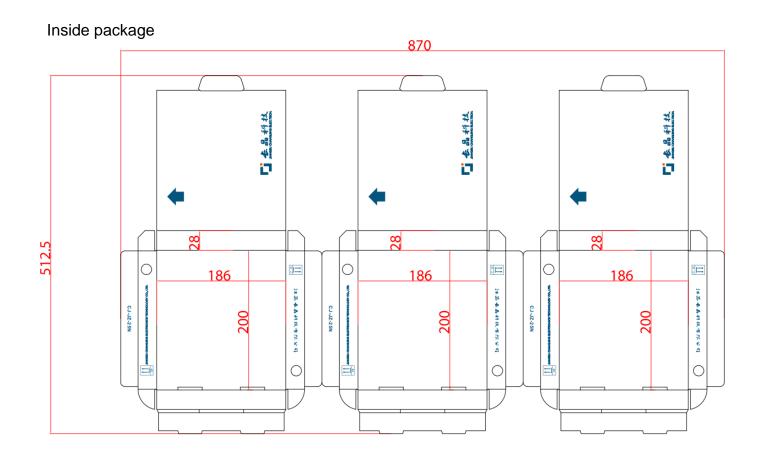


EMBOSSED TYPE DIMENSIONS

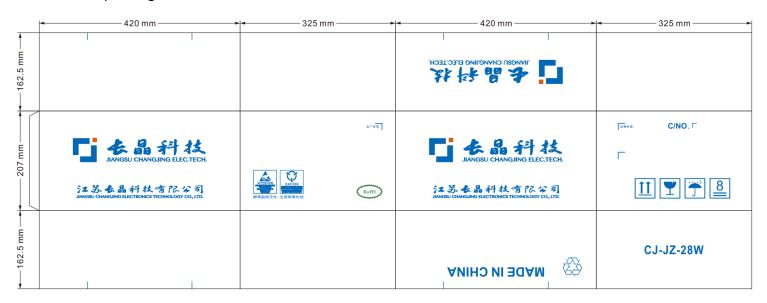


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#### **Package**



#### Outside package



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